

N-channel 100V 26.8 mΩ standard level MOSFET in TO220

Rev. 3 — 12 September 2011

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 1</u>	-	-	37	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	103	W
Tj	junction temperature		-55	-	175	°C
Static cha	racteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ T _j = 100 °C; see <u>Figure 12</u>	-	-	48	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{100000000000000000000000000000000000$	-	21	26.8	mΩ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I _D = 30 A;	-	9	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 50 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	30	-	nC
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy		-	-	59	mJ

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

SOT78 (TO-220AB)

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN027-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

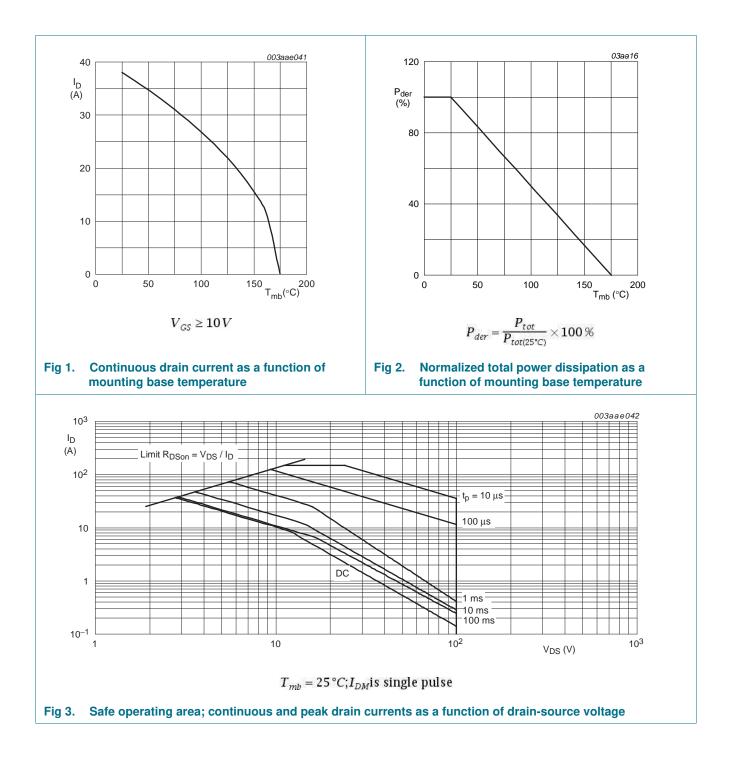
4. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	26	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	37	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	148	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	103	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-dra	in diode				
I _S	source current	T _{mb} = 25 °C	-	37	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	148	А
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 37 A; $V_{sup} \le$ 100 V; unclamped; R_{GS} = 50 Ω	-	59	mJ
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5. Thermal characteristics

SymbolParameterConditionsMinTypMaxUnitR _{th(j-mb)} thermal resistance from junction to mounting basesee Figure 4-0.81.46K/WR _{th(j-a)} thermal resistance from junction to ambientvertical in free air-60-K/W							
base	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$ thermal resistance from junction to ambient vertical in free air - 60 - K/W	$R_{th(j-mb)}$		see Figure 4	-	0.8	1.46	K/W
	R _{th(j-a)}	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

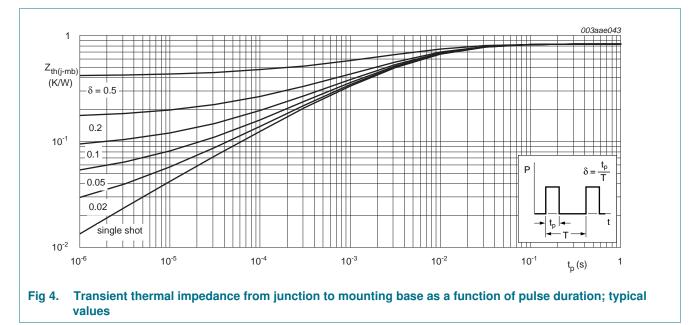


Table 5. Thermal characteristics

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6. Characteristics

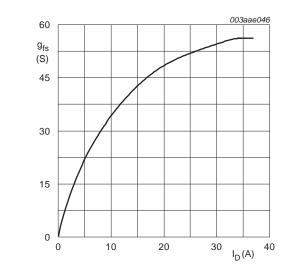
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
- Static char	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 0.25 mA; V _{GS} = 0 V; T _i = -55 °C	90	-	-	V
(I _D = 0.25 mA; V _{GS} = 0 V; T _i = 25 °C	100	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	4.8	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 125 °C	-	-	50	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.08	2	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	48	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; see <u>Figure 12</u>	-	59	75	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 13</u>	-	21	26.8	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz	-	0.92	-	Ω
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	I_D = 30 A; V_{DS} = 50 V; V_{GS} = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	30	-	nC
		$I_D = 0 \; A; V_{DS} = 0 \; V; V_{GS} = 10 \; V$	-	24	-	nC
Q _{GS}	gate-source charge	$I_D = 30 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	8	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 30 \text{ A}; \text{V}_{DS} = 50 \text{V}; \text{V}_{GS} = 10 \text{V};$ see Figure 14	-	4.8	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	3.4	-	nC
Q _{GD}	gate-drain charge	$I_D = 30 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	9	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 50 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	4.9	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1624	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{16}$	-	115	-	pF
C _{rss}	reverse transfer capacitance		-	74	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 1.7 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	14.4	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega; \ T_j = 25 \ ^{\circ}C$	-	11.4	-	ns
t _{d(off)}	turn-off delay time		-	29.6	-	ns
t _f	fall time		-	8.9	-	ns

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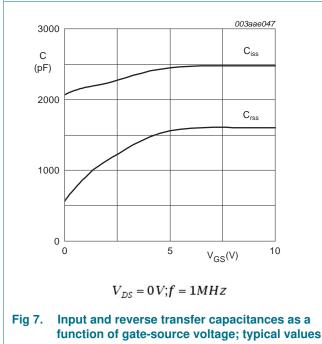
Table 6. Characteristics ...continued

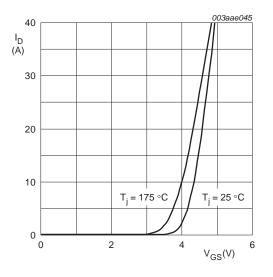
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain	n diode					
V_{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 10 \text{ A}; dI_{S}/dt = 100 \text{ A}/\mu\text{s};$	-	47	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 50 V$		91	-	nC



$T_j = 25 \,^{\circ}C; V_{DS} = 10 \, V$

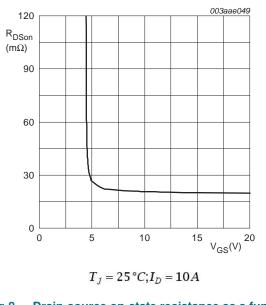






$$V_{DS} > I_D imes R_{DSon}$$



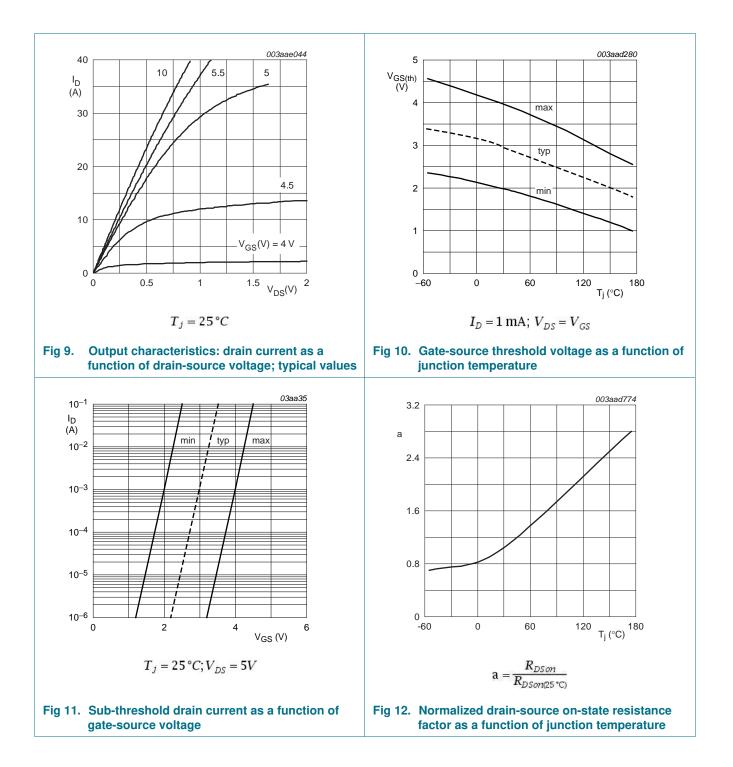




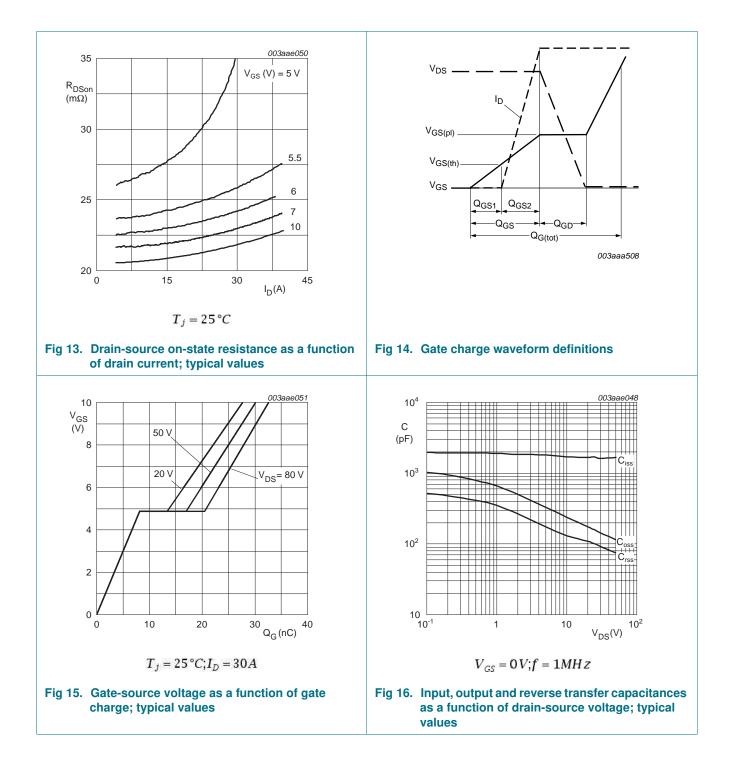
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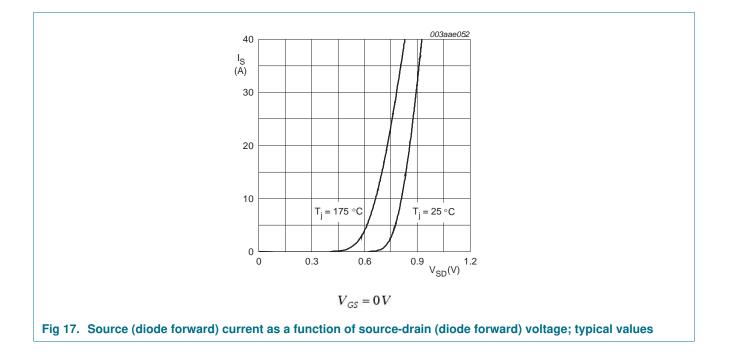
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Package outline 7.

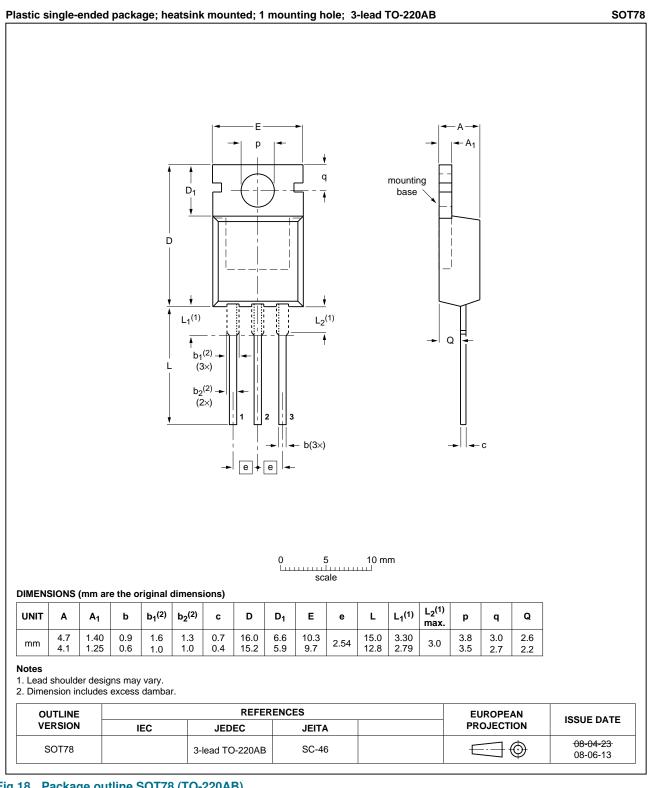


Fig 18. Package outline SOT78 (TO-220AB)

PSMN027-100PS **Product data sheet**

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8. Revision history

Table 7. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN027-100PS v.3	20110912	Product data sheet	-	PSMN027-100PS v.2
Modifications:	Status changeVarious change	d from objective to product. es to content.		
PSMN027-100PS v.2	20100219	Objective data sheet	-	PSMN027-100PS v.1

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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